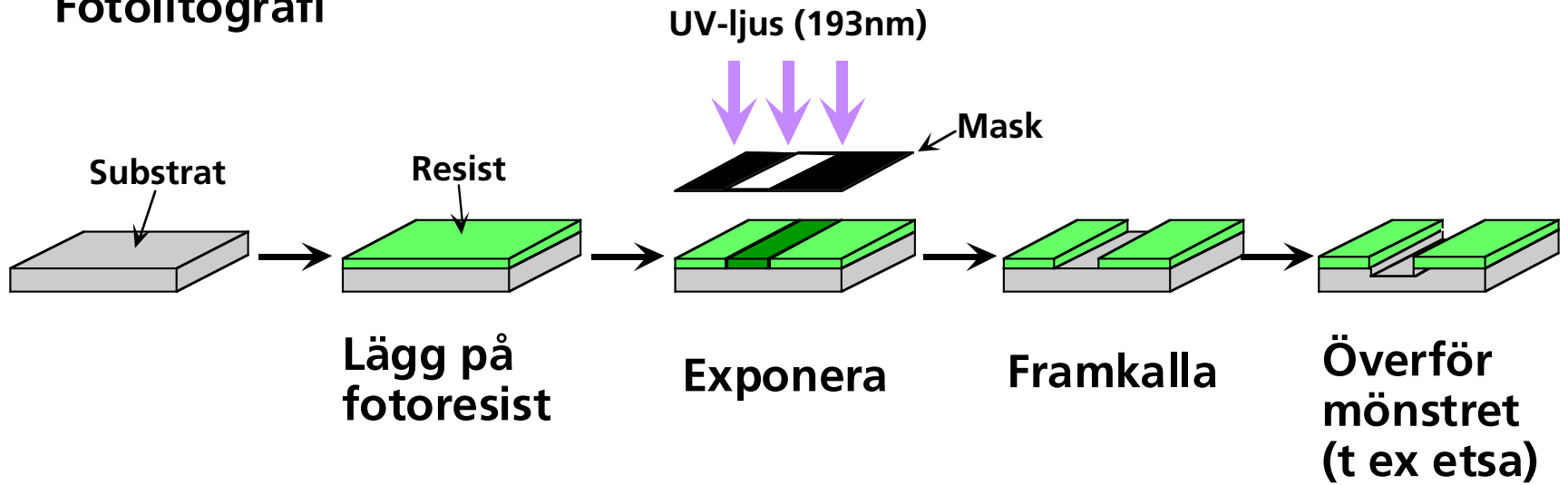
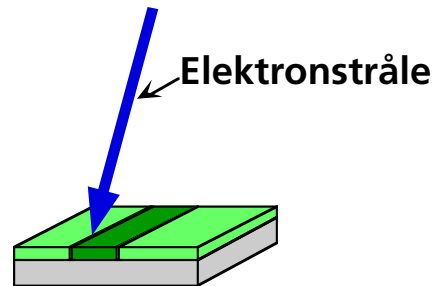


Tillverkning 1: Litografi

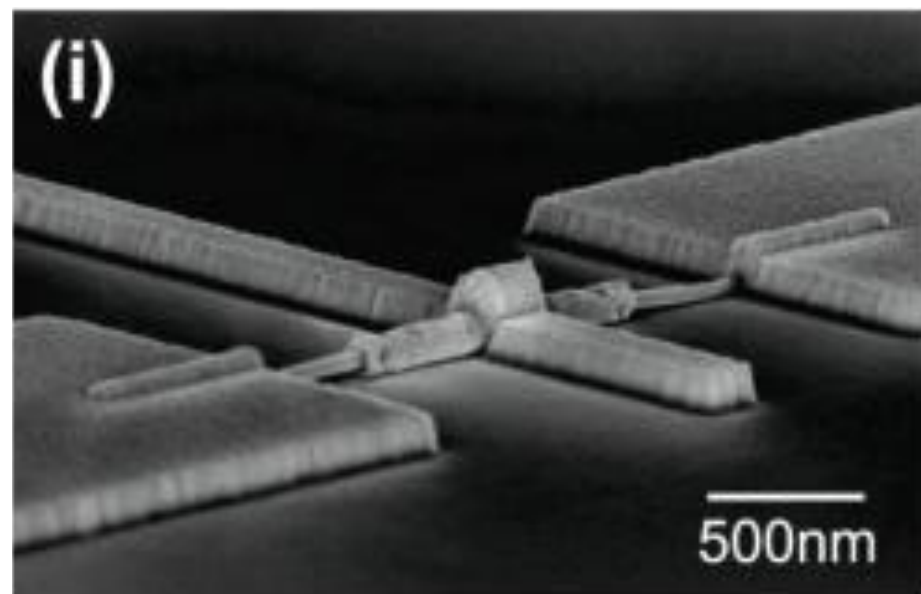
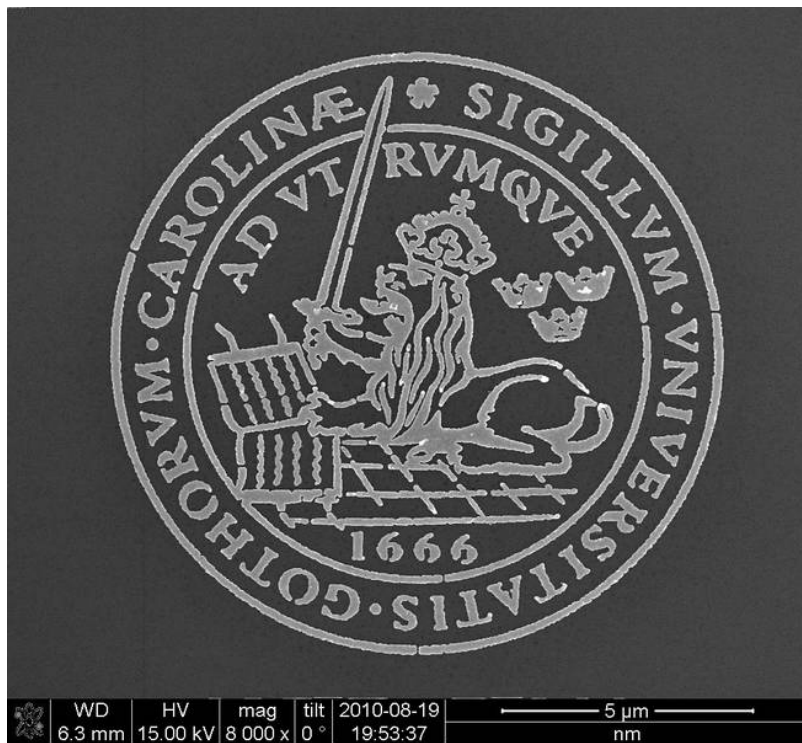
Fotolitografi



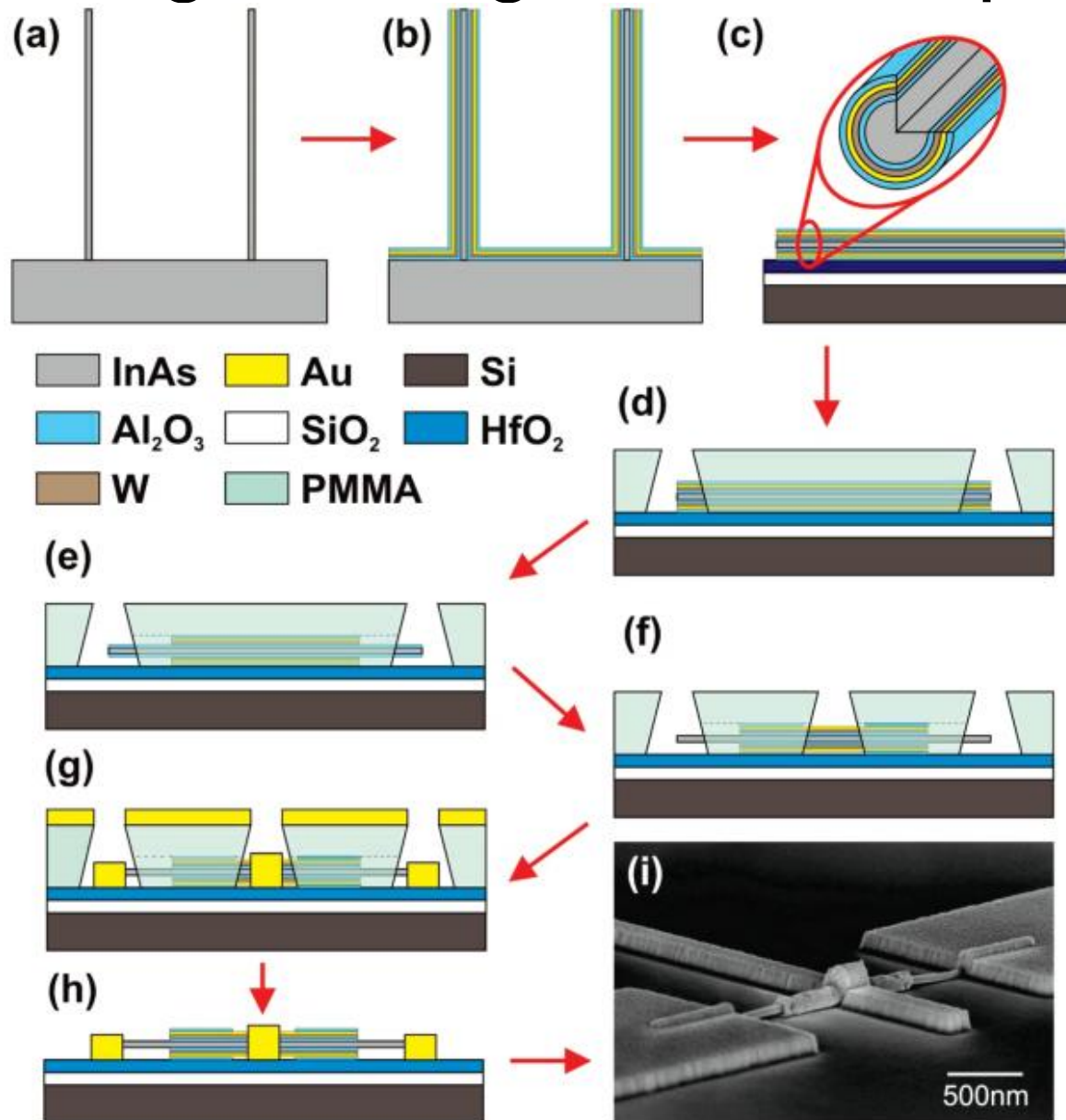
Elektronstrålelitografi



Litografi

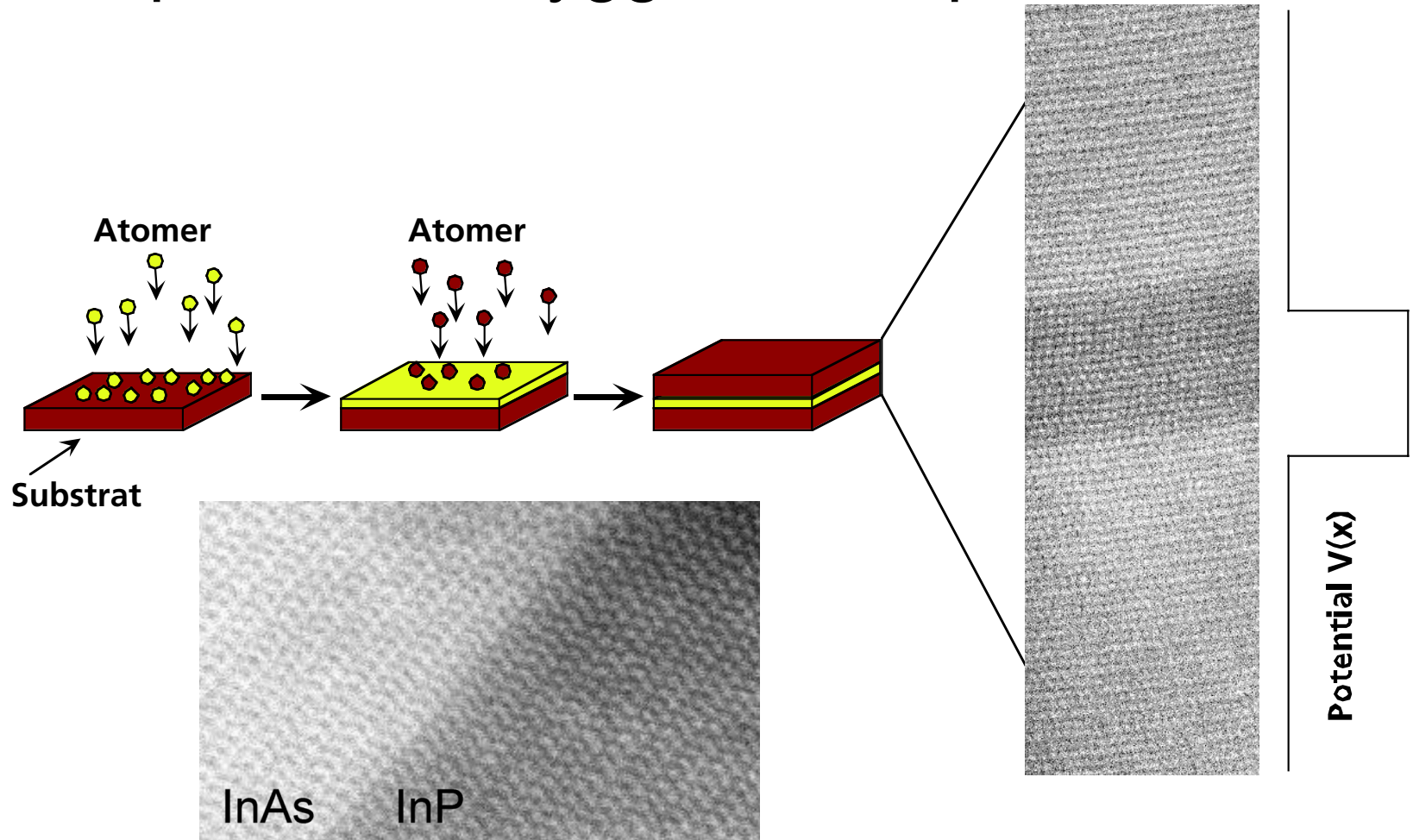


Flera steg för att göra en komponent



Tillverkning 2:

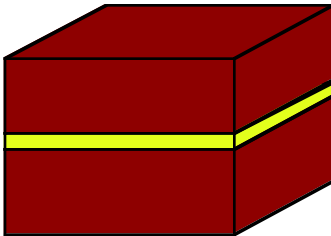
Epitaxi – att bygga vidare på kristaller



Perfekt övergång mellan materialen
med kontroll på atomnivå.

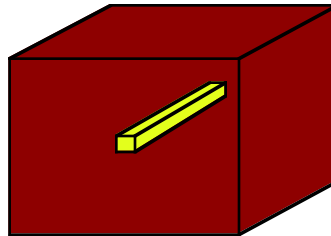
Kvantstrukturer

2D



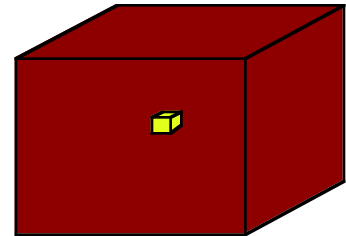
Kvantbrunn

1D



Kvantråd

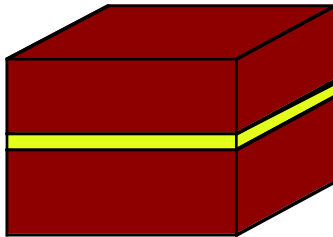
0D



Kvantprick

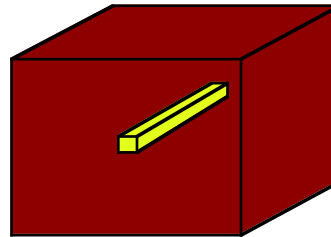
Kvantstrukturer

2D



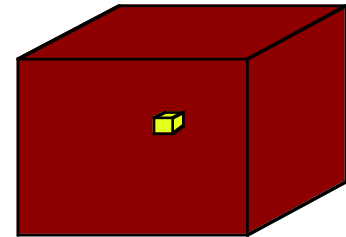
Kvantbrunn

1D



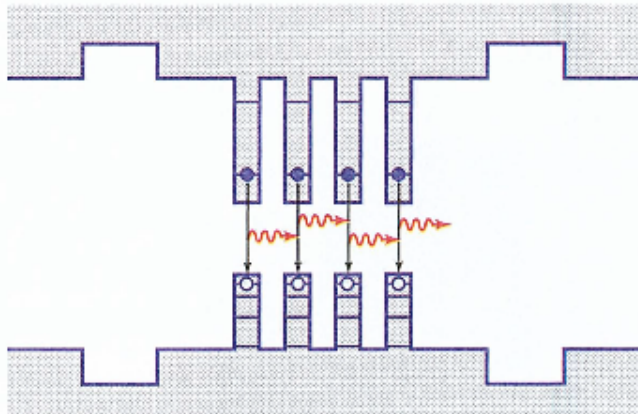
Kvantråd

0D



Kvantprick

Exempel: effektivare LED

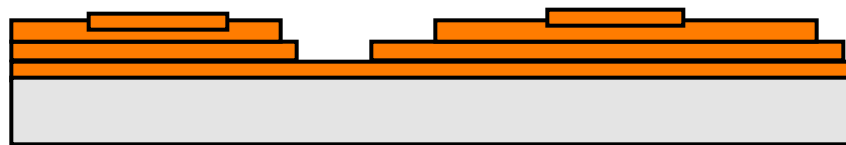


Självordnande kvantprickar

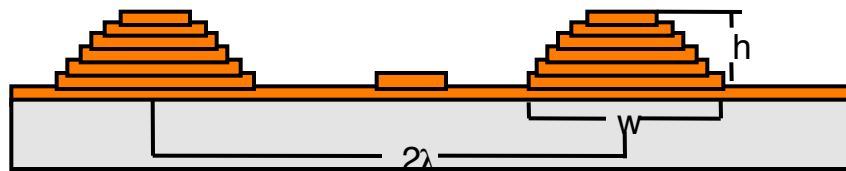
Step1: deposition of a pseudomorphic 2D epilayer:



Step2: 3D nucleation and reorganization:



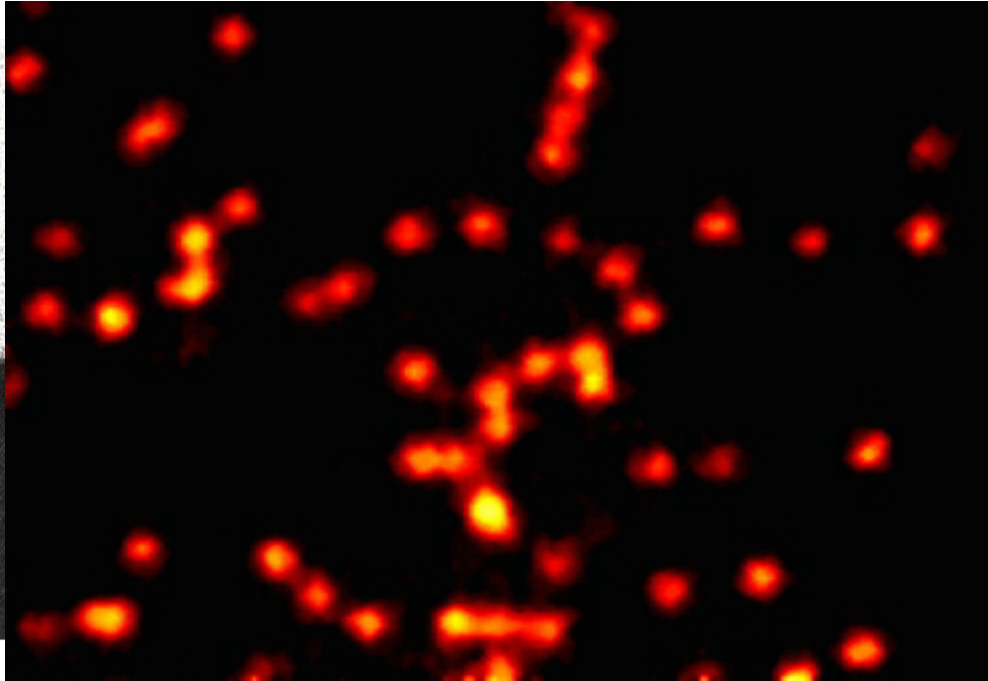
Step3: growth and ripening of 3D islands:



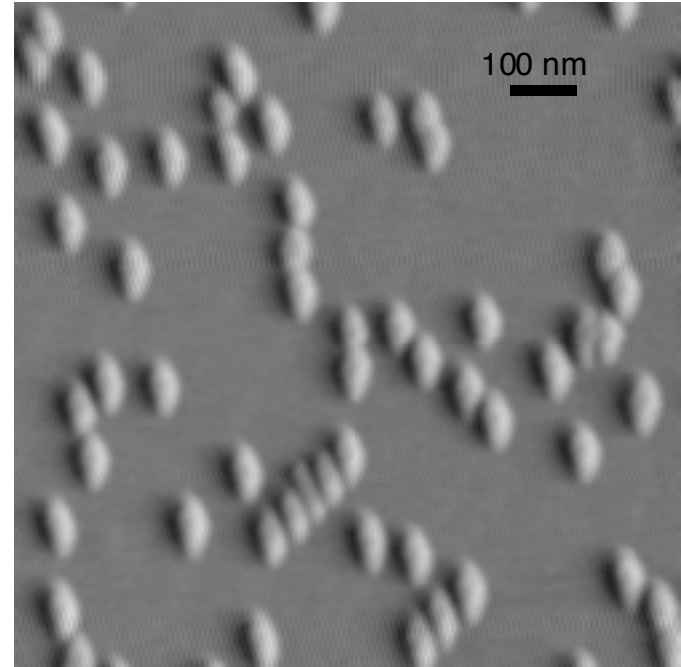
Dessa öar kan användas som kvantprickar

Materialsystem: InP/GaInP, InAs/InP, InAs/GaAs, Ge/Si

InP kvantprick på GaInP



TEM-bild
Luminescens-bild



AFM-bild

3D island **InP**/GaInP

MOVPE 580 °C

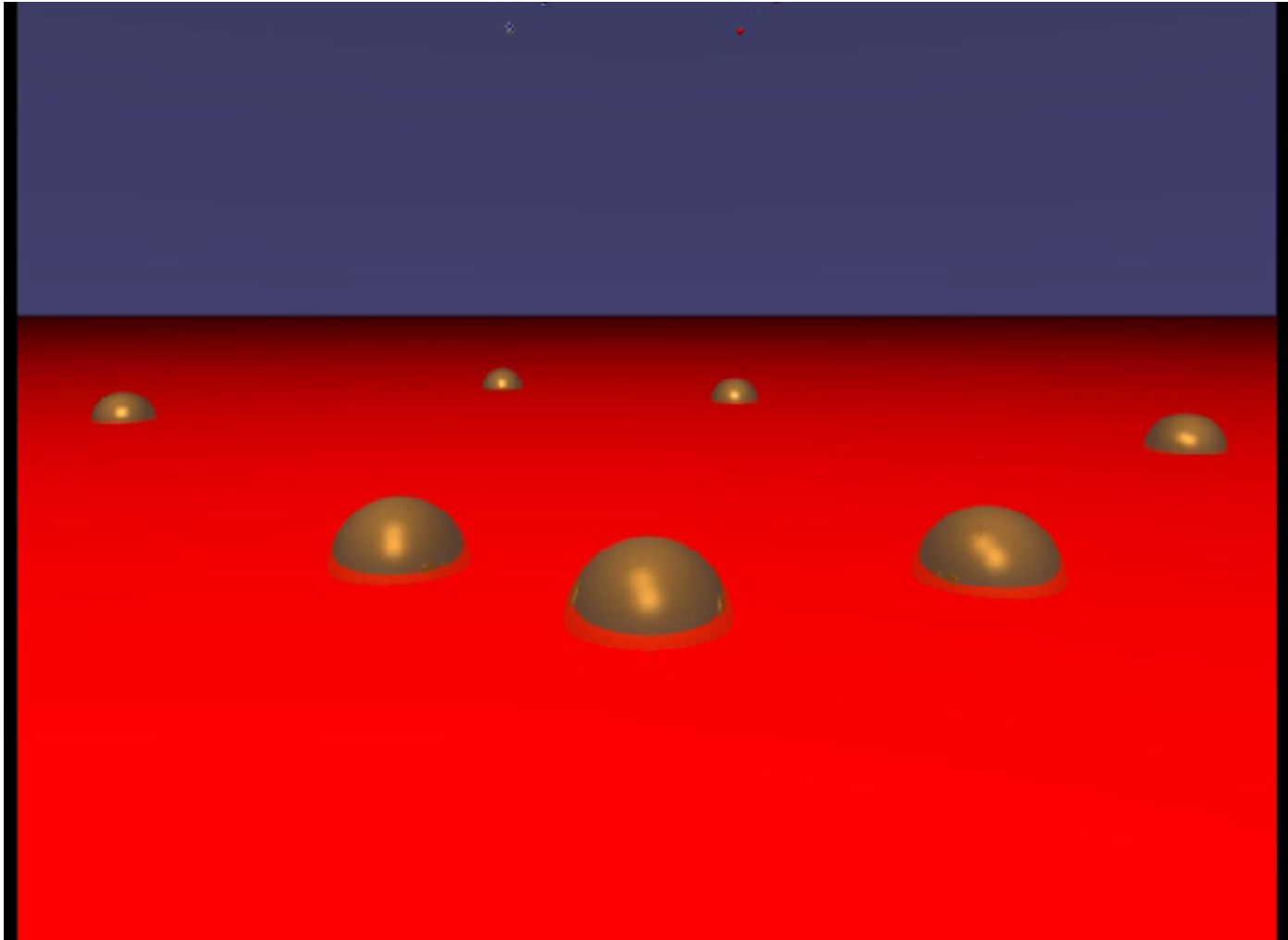
(K. Georgsson et al.

APL 67 (1995) 2981)

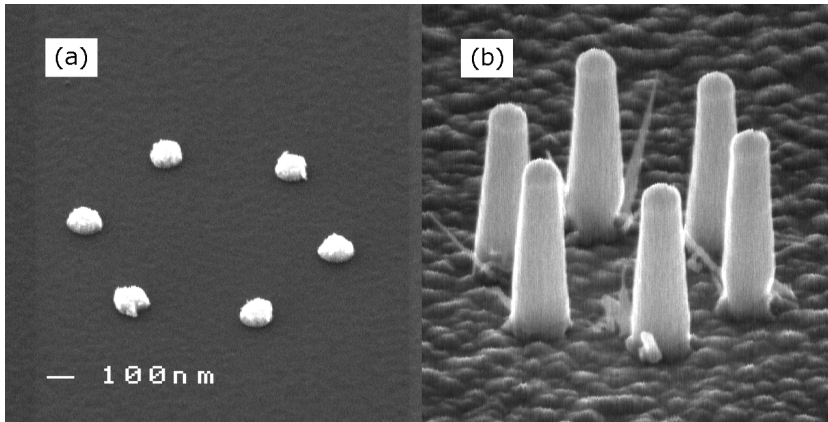
Top-down eller bottom-up?



Vår specialitet: Nanotrådar
10 nm - 100 nm i diameter, några μm långa

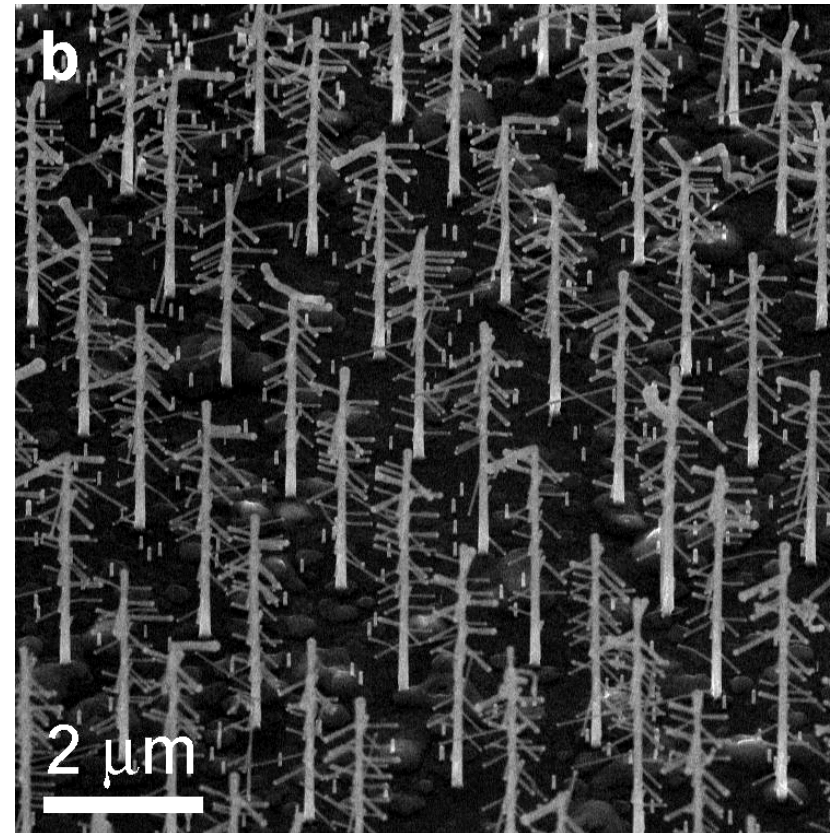
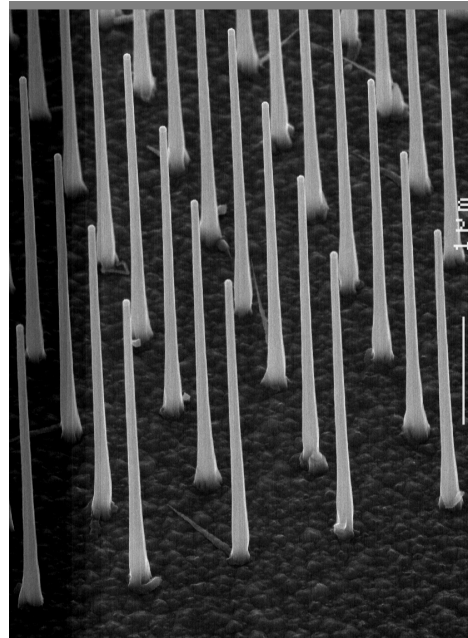


Nanotrådar



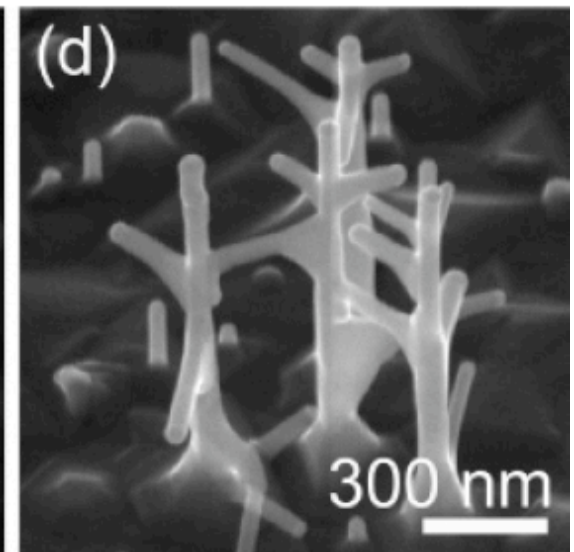
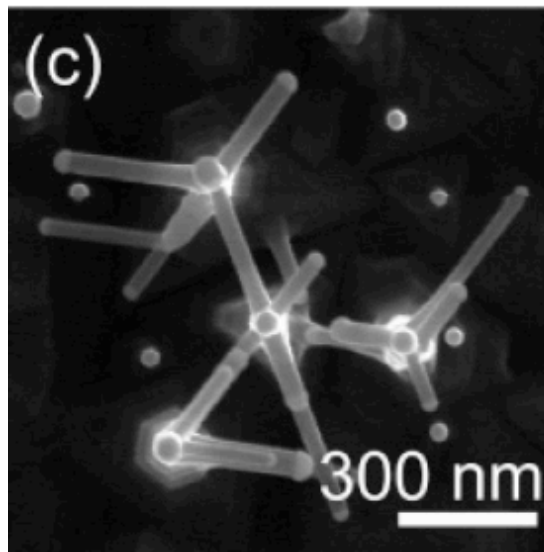
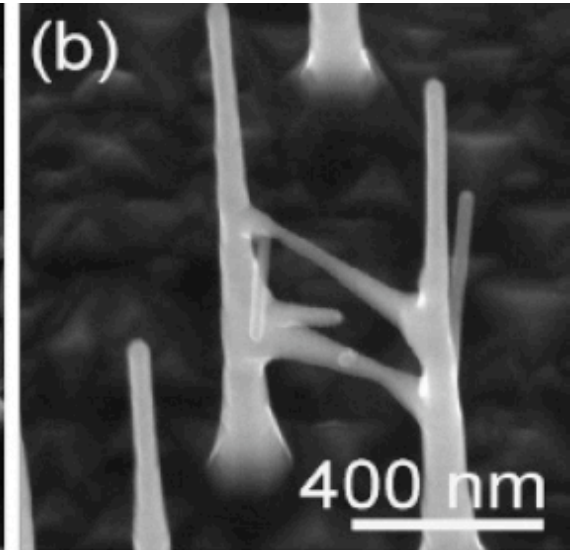
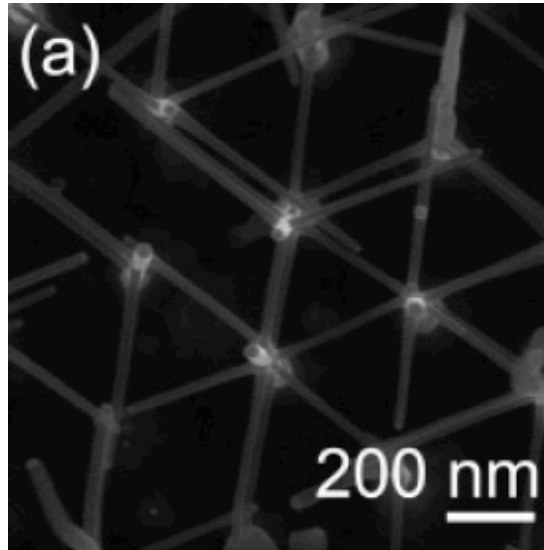
Ordnade rader av GaP nanoträd

Nanotrådar
odlade från
ordnade rader
med Au-partiklar
definierade med
elektronstråle-
litografi



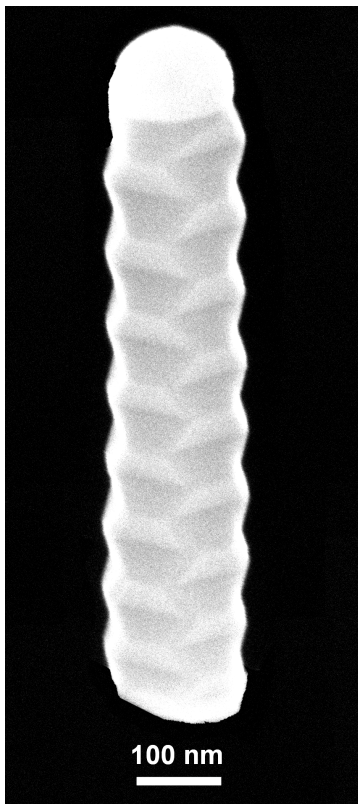
Nanotrådar

Sammanväxta till
tredimensionella
nätverk

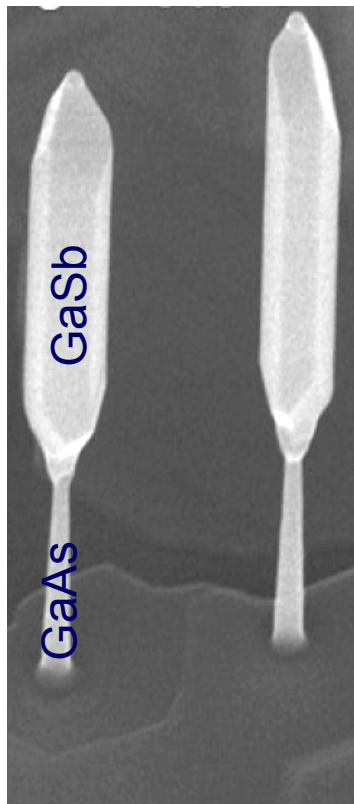


Varför nanotrådar?

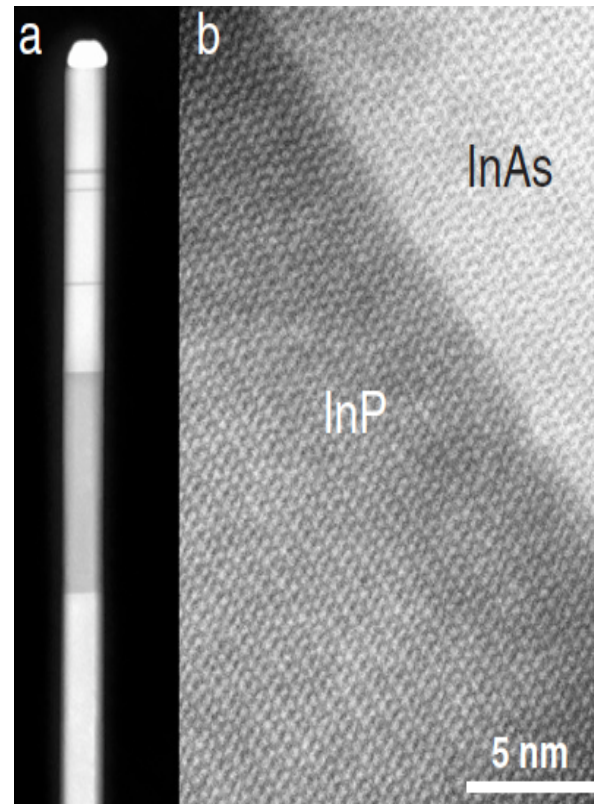
Perfekt kristallstruktur



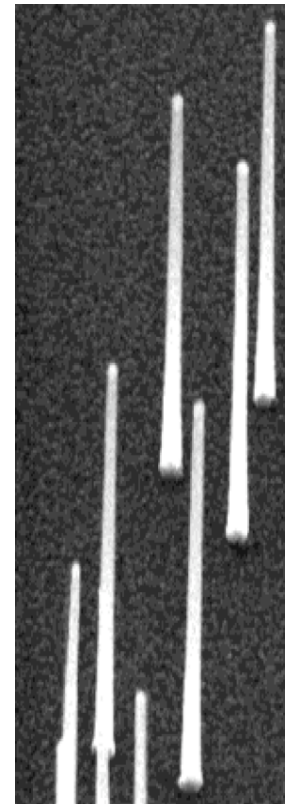
Nya materialkombinationer



Atomärt skarpa gränssytor



På "billiga" kiselsubstrat



Halvledare

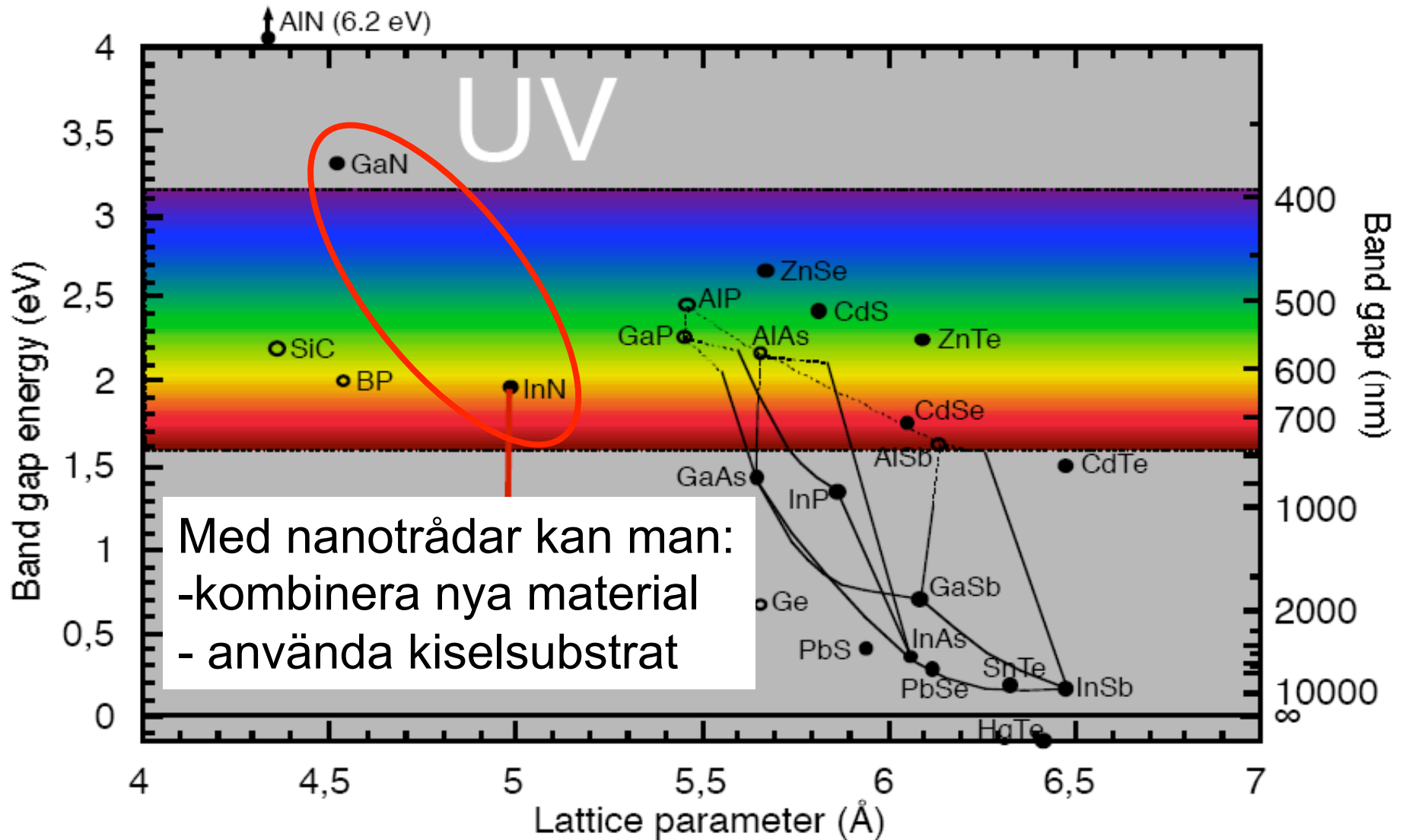
- Grupp IV: Si, Ge
Transistorer, CCD, solceller, *indirekt bandgap*
- Grupp III-V: GaP, GaAs, InGaAsP...
LED, lasrar, detektore
- Grupp III-N: GaN, InGaN...
Blå (& vita) LED, UV lasrar
- Grupp II-VI: HgCdTe...
IR-kameror

	II	III	IV	V	VI
2		5 B	6 C	7 N	8 O
3	12 Mg	13 Al	14 Si	15 P	16 S
4	30 Zn	31 Ga	32 Ge	33 As	34 Se
5	48 Cd	49 In	50 Sn	51 Sb	52 Te
6	80 Hg		82 Pb		

Periodiska systemet

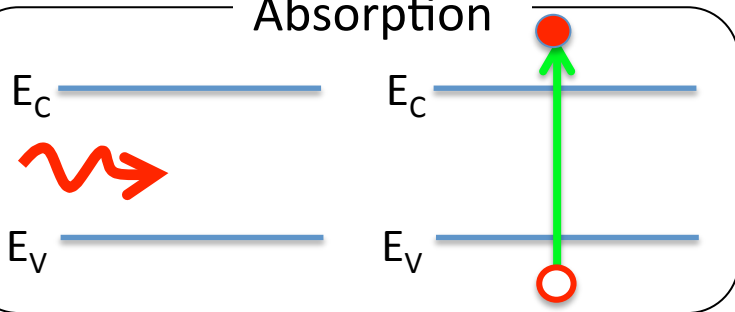
(åtminstone den del som är
viktig för en halvledarfysiker)

Band gaps of different semiconductors

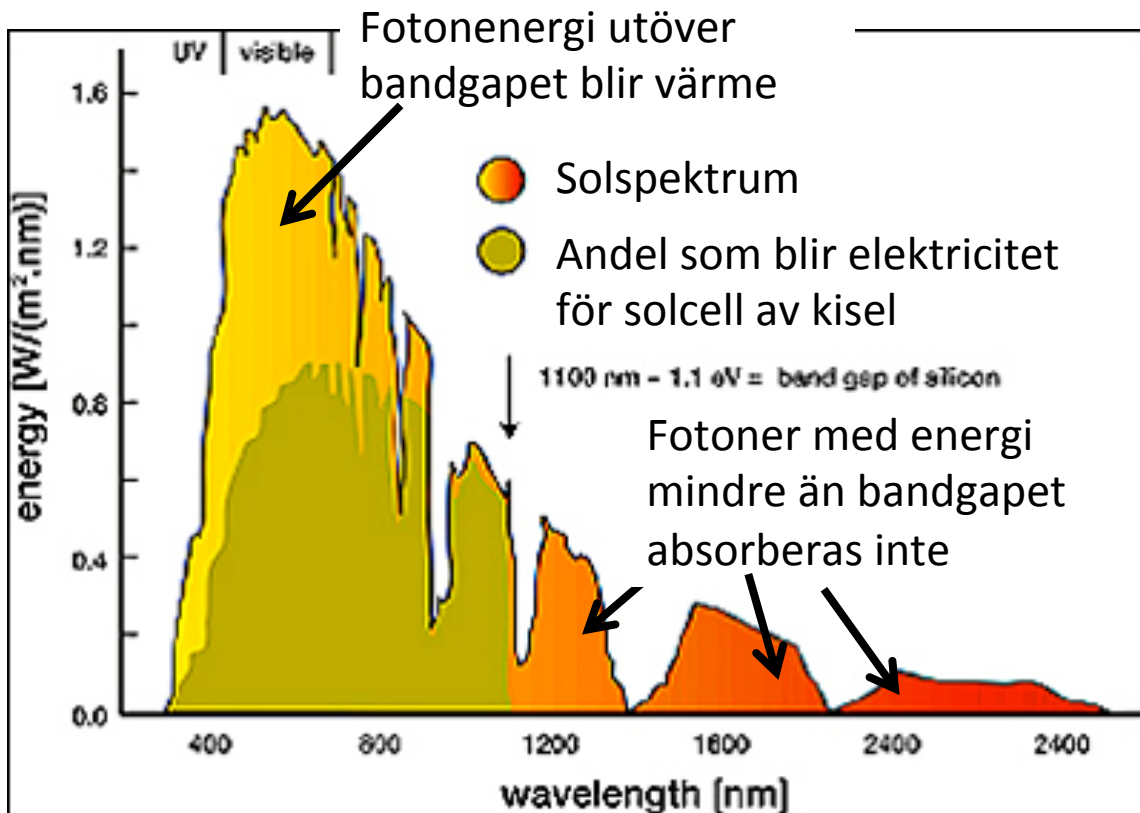


Solcell

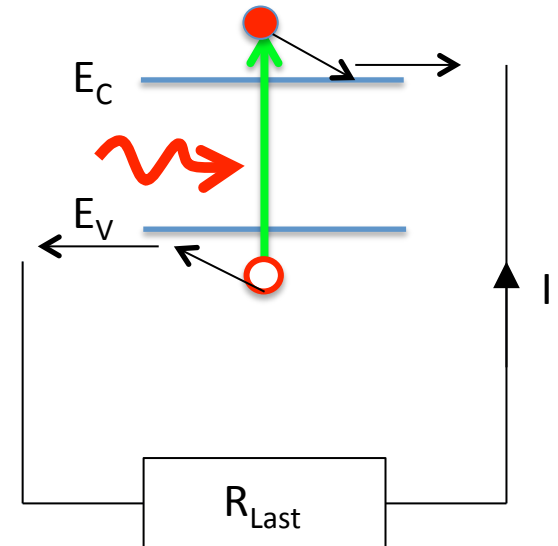
Absorption



Kostnad
Livslängd
Miljö



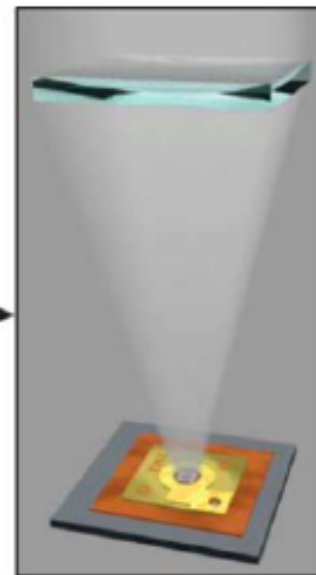
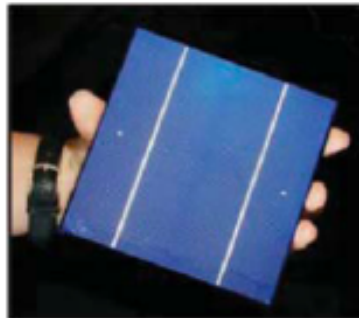
<http://solarcellcentral.com>



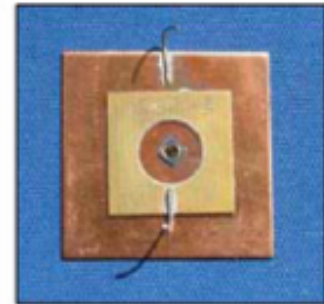
High-Efficiency Multijunction Solar Cells

Frank Dimroth and Sarah Kurtz

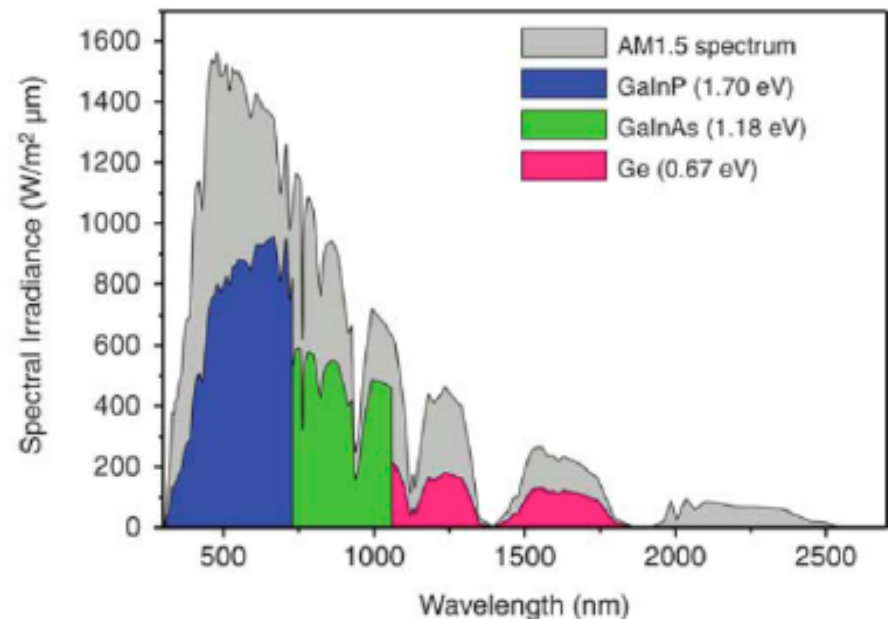
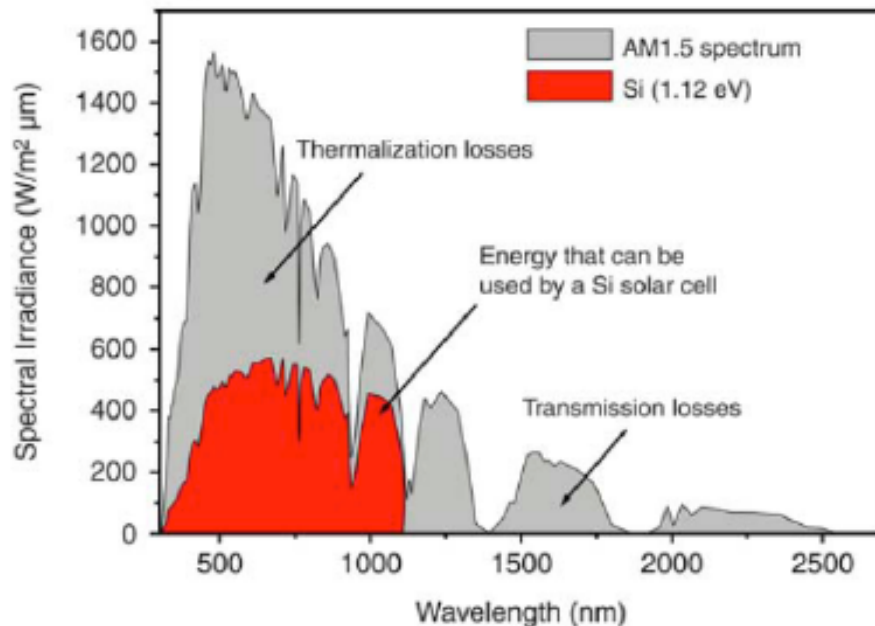
100 cm² Si
solar cell area



100 cm² lens area



5 mm² multijunction
solar cell



85%



Varför bara 20% effektivitet?

43% Elektricitet → Ljus

Mer forskning krävs om material & kontakter
(Redan idag är 80% möjligt vid låga effekter)

56% Ljus → Ljus (innebär förlust som värme)
Ersätt lyspulvret med grön och röd LED

85% Ljus → synintryck

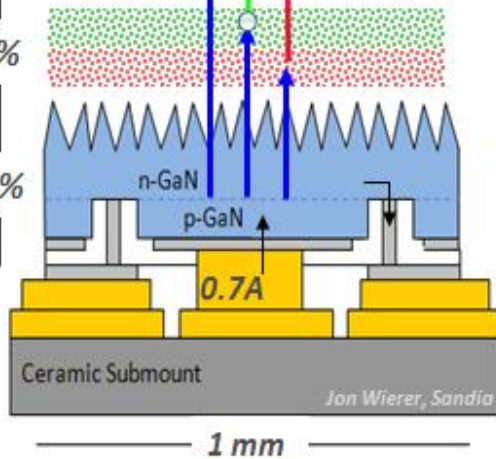
Optimera färgerna hos lysdioderna
Särskilt grönt kräver mer utveckling

Efficiencies

Lyspulver

56%

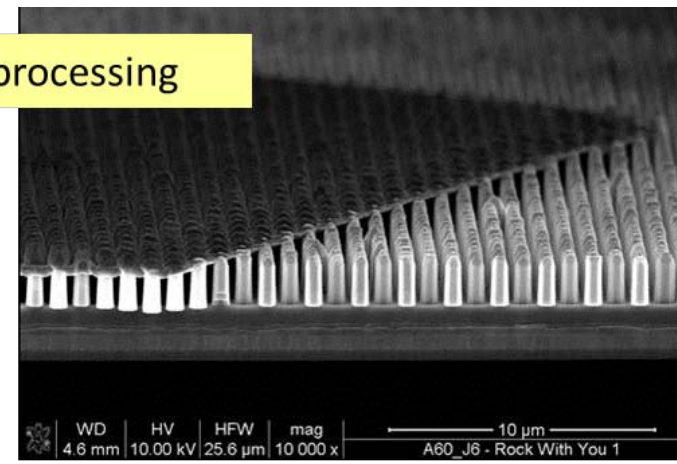
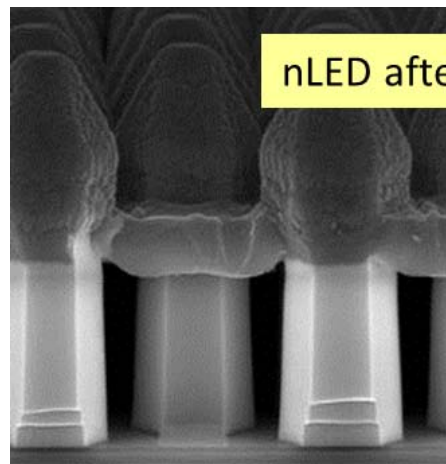
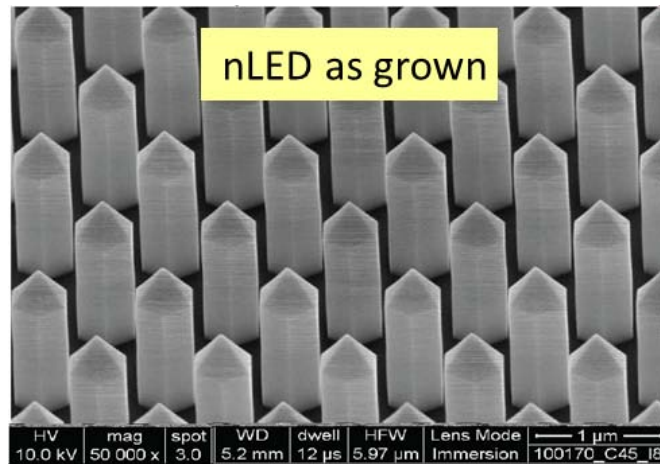
43%



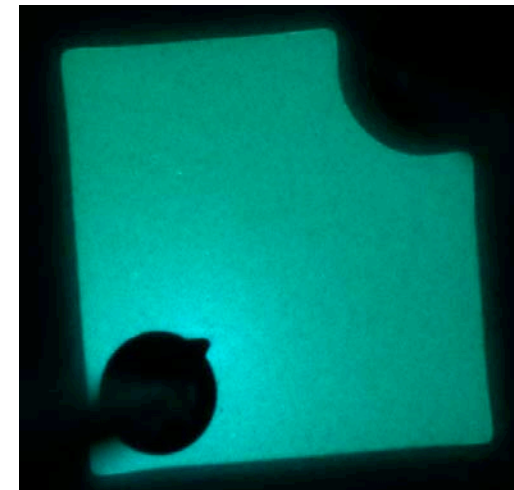
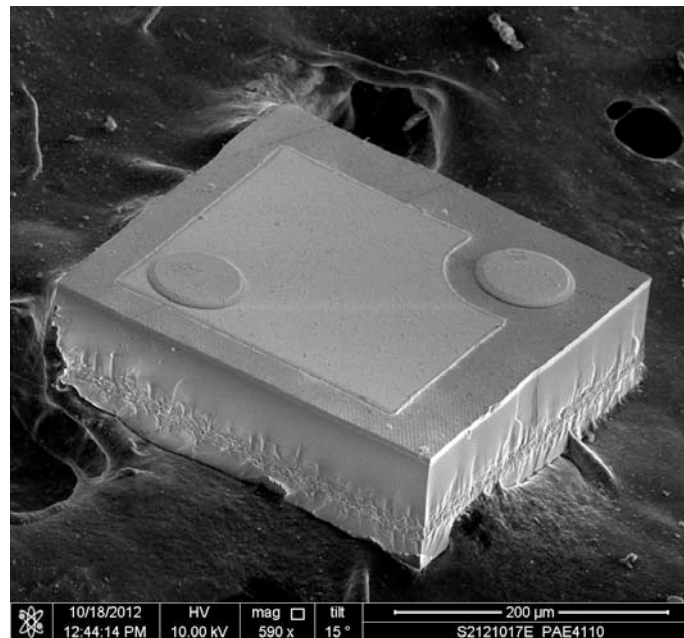
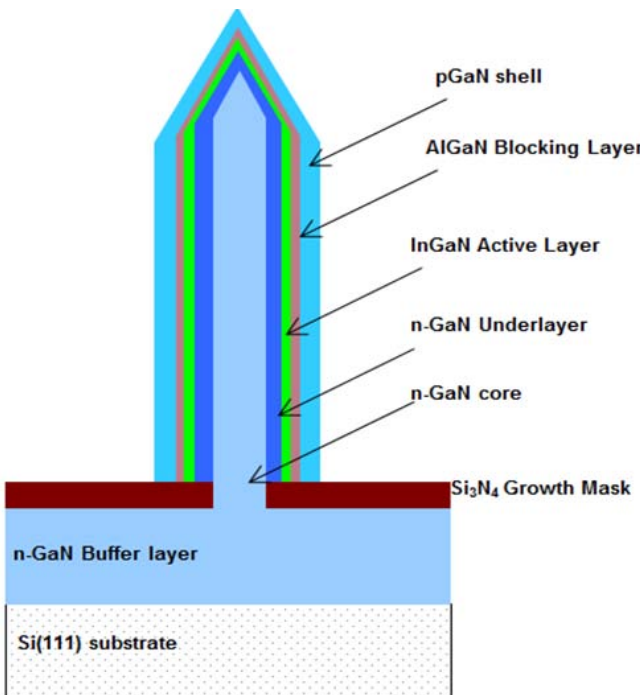
Blå lysdiod

I vår forskning använder vi
nanotrådar av halvledare för att
lösa de här problemen – och
dessutom billigare!

nLEDs

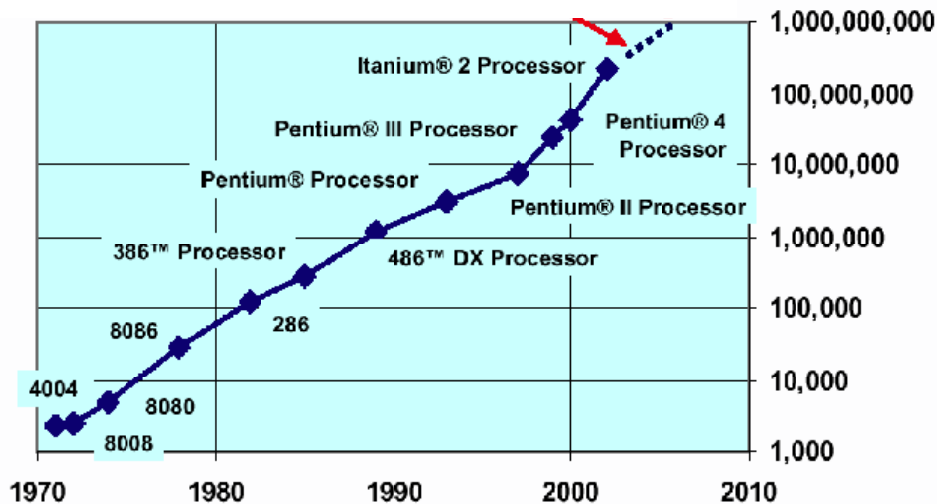


nLED after processing

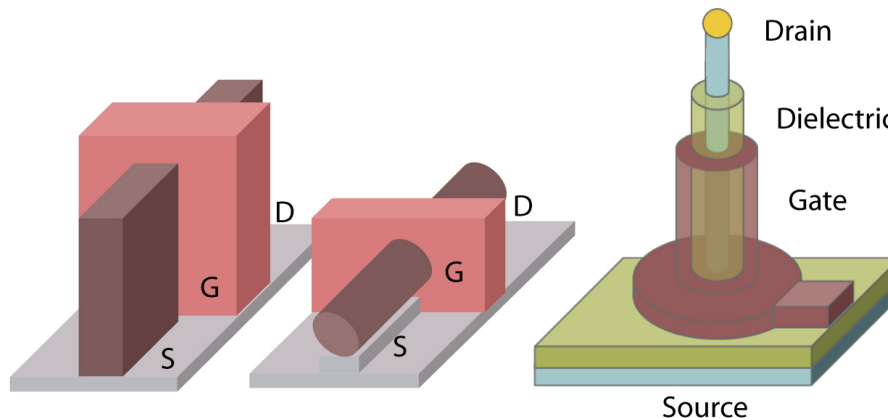
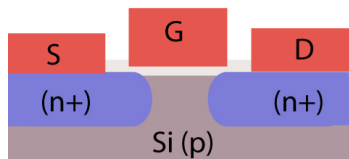
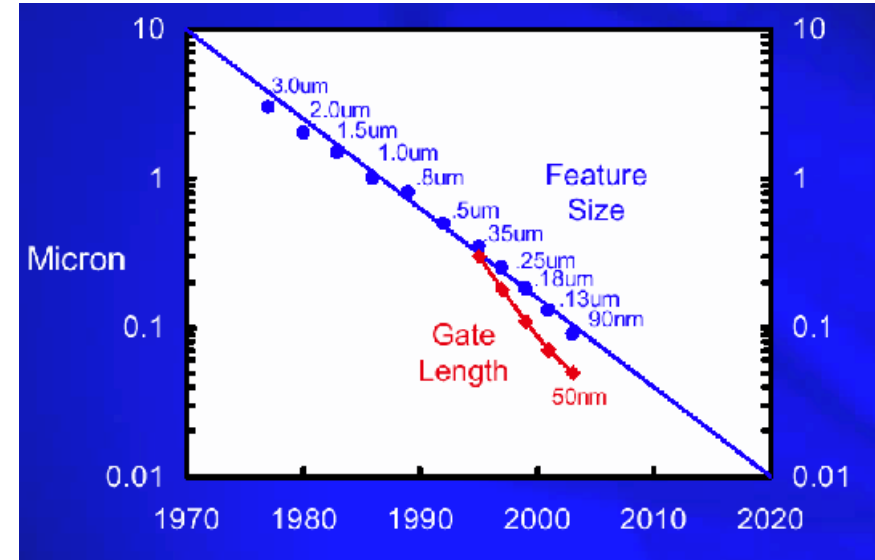


Elektronik

Moore's lag: antalet transistorer ökar
exponentiellt
(fördubblas vartannat år)



... transistorernas storlek minskar
exponentiellt



Nya transistorkoncept
krävs, t ex
nanotrådsbaserad
fälteffekttransistor (FET)